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Docket No.: M4065.1019/P1019
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Letters Patent of:
Joseph F. Brooks

Patent No.: 7,098,068

Issued: August 29, 2006

For: METHOD OF FORMING A
CHALCOGENIDE MATERIAL
CONTAINING DEVICE

Certificate
OCT 10 2006
of Correction

REQUEST FOR CERTIFICATE OF CORRECTION
PURSUANT TO 37 CFR 1.322

Attention: Certificate of Correction Branch
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Upon reviewing the above-identified patent, Patentee noted omissions and typographical errors which should be corrected.

In the Claims, the PTO made the following omissions of text to be corrected:

Claim 42, column 10, line 32, "a layer" should read --a first layer--;

Claim 42, column 10, line 34, "the layer" should read --the first layer--; and

Claim 42, column 10, line 49, "Ge_xSe_{100-x}" should read --Ge_xSe_{100-x}--.

OCT 12 2006

In the Other Publications portion of the References Cited section, the PTO made the following errors to be corrected:

“Afifi, M.A.; Labib, H.H.; Fouad, A.A.; Electrical & thermal conductivity of the amorphous semiconductor $\text{Ge}_x\text{Se}_{1-x}$, Egypt. J. Phys. 17 (1986) 335-342.”

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“Fischer-Colbrie, A.; Bienenstock, A.; Fuoss, P.H.; Marcus, M.A., Structure and bonding in photodiffuses amorphous Ag-GeSe_2 thin films, Phys. Rev. B 38 (1988) 12388-12403.”

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“Mitkiva, M.; Kozicki, M.N., Silver incorporation in Ge-Se glasses used in programmable metallization cell devices, J. Non-Cryst. Solids 299-302 (2002) 1023-1027.”

Should read

--Mitkova, M.; Kozicki, M.N., Silver incorporation in Ge-Se glasses used in programmable metallization cell devices, J. Non-Cryst. Solids 299-302 (2002) 1023-1027.--.

OCT 12 2006

The errors were not in the application as filed or amended by Applicant;
accordingly no fee is required.

Transmitted herewith is a proposed Certificate of Correction effecting such
amendment. Patentee respectfully solicits the granting of the requested Certificate of
Correction.

Dated: October 5, 2006

Respectfully submitted,

By 

Thomas J. D'Amico

Registration No.: 28,371

Elizabeth Parsons

Registration No.: 52,499

DICKSTEIN SHAPIRO LLP

1825 Eye Street, NW

Washington, DC 20006-5403

(202) 420-2200

Attorneys for Applicant

**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

Page 1 of 2

PATENT NO. : 7,098,068
APPLICATION NO. : 10/796,109
ISSUE DATE : August 29, 2006
INVENTORS : Joseph F. Brooks

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the Claims, the following omissions are corrected:

Claim 42, column 10, line 32, "a layer" should read --a first layer--;

Claim 42, column 10, line 34, "the layer" should read --the first layer--; and

Claim 42, column 10, line 49, "Ge_xSe₁₀₀." should read --Ge_xSe_{100-x}--.

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Should read

MAILING ADDRESS OF SENDER (Please do not use customer number below):

Thomas J. D'Amico
DICKSTEIN SHAPIRO LLP
1825 Eye Street, NW
Washington, DC 20006-5403

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--Fischer-Colbrie, A.; Bienenstock, A.; Fuoss, P.H.; Marcus, M.A., Structure and bonding in photodiffused amorphous Ag-GeSe₂ thin films, Phys. Rev. B 38 (1988) 12388-12403.--;

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DICKSTEIN SHAPIRO LLP
1825 Eye Street, NW
Washington, DC 20006-5403

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